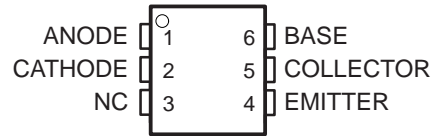


## COMPATIBLE WITH STANDARD TTL INTEGRATED CIRCUITS

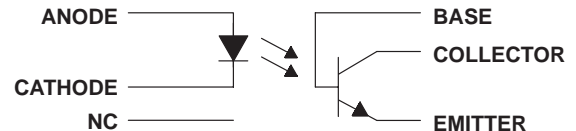
- Gallium-Arsenide-Diode Infrared Source  
Optically Coupled to a Silicon npn Phototransistor
- High Direct-Current Transfer Ratio
- High-Voltage Electrical Isolation  
1.5-kV, 2.5-kV, or 3.55-kV Rating
- High-Speed Switching  
 $t_r = 7 \mu\text{s}$ ,  $t_f = 7 \mu\text{s}$  Typical
- Typical Applications Include Remote Terminal Isolation, SCR and Triac Triggers, Mechanical Relays and Pulse Transformers
- Safety Regulatory Approval  
UL/CUL, File No. E65085

DCJT OR 6-TERMINAL DUAL-IN-LINE PACKAGE  
(TOP VIEW)



†4N35 only  
NC – No internal connection

schematic



### absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)†

Input-to-output peak voltage (8-ms half sine wave):	4N35	3.55 kV
	4N36	2.5 kV
	4N37	1.5 kV
Input-to-output root-mean-square voltage (8-ms half sine wave):	4N35	2.5 kV
	4N36	1.75 kV
	4N37	1.05 kV
Collector-base voltage		70 V
Collector-emitter voltage (see Note 1)		30 V
Emitter-base voltage		7 V
Input-diode reverse voltage		6 V
Input-diode forward current:		
Continuous		60 mA
Peak (1 $\mu\text{s}$ , 300 pps)		3 A
Phototransistor continuous collector current		100 mA
Continuous total power dissipation at (or below) 25°C free-air temperature:		
Infrared-emitting diode (see Note 2)		100 mW
Phototransistor (see Note 3)		300 mW
Continuous power dissipation at (or below) 25°C lead temperature:		
Infrared-emitting diode (see Note 4)		100 mW
Phototransistor (see Note 5)		500 mW
Operating temperature range, $T_A$		-55°C to 100°C
Storage temperature range, $T_{stg}$		-55°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds		260°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES:
1. This value applies when the base-emitter diode is open-circuited.
  2. Derate linearly to 100°C free-air temperature at the rate of 1.33 mW/°C.
  3. Derate linearly to 100°C free-air temperature at the rate of 4 mW/°C.
  4. Derate linearly to 100°C lead temperature at the rate of 1.33 mW/°C. Lead temperature is measured on the collector lead 0.8 mm (1/32 inch) from the case.
  5. Derate linearly to 100°C lead temperature at the rate of 6.7 mW/°C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

 **TEXAS  
INSTRUMENTS**

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# 4N35, 4N36, 4N37 OPTOCOUPERS

SOES021C – NOVEMBER 1981 – REVISED APRIL 1998

## electrical characteristics at 25°C free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = 100 \mu A, I_E = 0, I_F = 0$	70†			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = 10 mA, I_B = 0, I_F = 0$	30†			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = 100 \mu A, I_C = 0, I_F = 0$	7†			V
$I_R$	Input diode static reverse current	$V_R = 6 V$			10†	$\mu A$
$I_{IO}$	Input-to-output current	$V_{IO} = \text{rated peak value}, t = 8 ms$			100	mA
$I_{C(on)}$	On-state collector current	$V_{CE} = 10 V, I_F = 10 mA, I_B = 0$	10†			mA
		$V_{CE} = 10 V, I_F = 10 mA, I_B = 0, T_A = -55^\circ C$	4†			
		$V_{CE} = 10 V, I_F = 10 mA, I_B = 0, T_A = 100^\circ C$	4†			
$I_{C(off)}$	Off-state collector current	$V_{CE} = 10 V, I_F = 0, I_B = 0$		1	50	nA
		$V_{CE} = 30 V, I_F = 0, I_B = 0, T_A = 100^\circ C$			500†	$\mu A$
$h_{FE}$	Transistor static forward current transfer ratio	$V_{CE} = 5 V, I_C = 10 mA, I_F = 0$		500		
$V_F$	Input diode static forward voltage	$I_F = 10 mA$	0.8†		1.5†	V
		$I_F = 10 mA, T_A = -55^\circ C$	0.9†		1.7†	
		$I_F = 10 mA, T_A = 100^\circ C$	0.7†		1.4†	
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C = 0.5 mA, I_F = 10 mA, I_B = 0 mA$			0.3†	V
$r_{IO}$	Input-to-output internal resistance	$V_{IO} = 500 V, \text{ See Note 6}$	10 <sup>11</sup> †			$\Omega$
$C_{io}$	Input-to-output capacitance	$V_{IO} = 0, f = 1 MHz, \text{ See Note 6}$		1	2.5†	pF

† JEDEC registered data

NOTE 6: These parameters are measured between both input-diode leads shorted together and all the phototransistor leads shorted together.

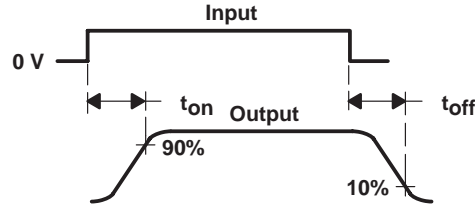
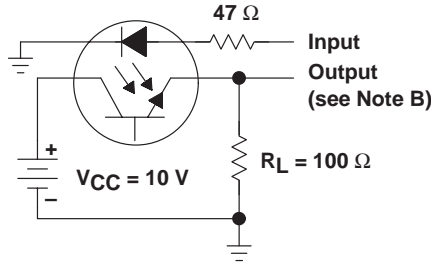
## switching characteristics at 25°C free-air temperature†

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{on}$	Time-on time	$V_{CC} = 10 V, I_{C(on)} = 2 mA,$		7	10	$\mu s$
$t_{off}$	Turn-off time	$R_L = 100 \Omega, \text{ See Figure 1}$		7	10	

† JEDEC registered data



PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT

VOLTAGE WAVEFORMS

- NOTES: A. The input waveform is supplied by a generator with the following characteristics:  $Z_O = 50 \Omega$ ,  $t_r \leq 15 \text{ ns}$ , duty cycle  $\approx 1\%$ ,  $t_W = 100 \mu\text{s}$ .  
 B. The output waveform is monitored on an oscilloscope with the following characteristics:  $t_r \leq 12 \text{ ns}$ ,  $R_{in} \geq 1 \text{ M}\Omega$ ,  $C_{in} \leq 20 \text{ pF}$ .

Figure 1. Switching Times

TYPICAL CHARACTERISTICS

OFF-STATE COLLECTOR CURRENT  
vs  
FREE-AIR TEMPERATURE

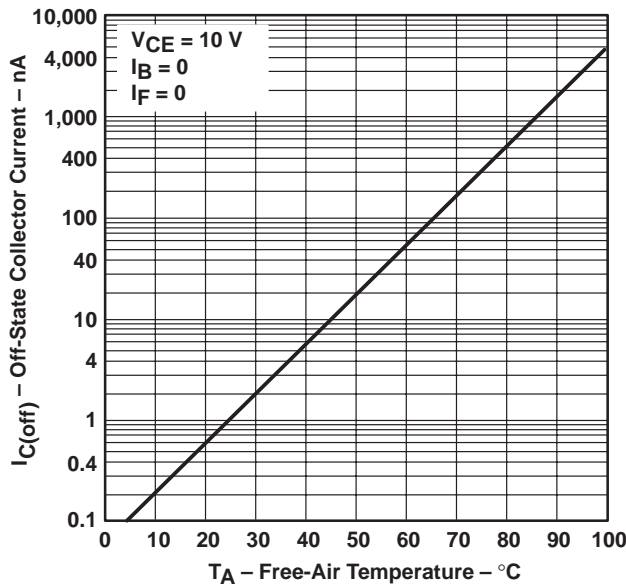


Figure 2

TRANSISTOR STATIC FORWARD  
CURRENT TRANSFER RATIO (NORMALIZED)  
vs  
ON-STATE COLLECTOR CURRENT

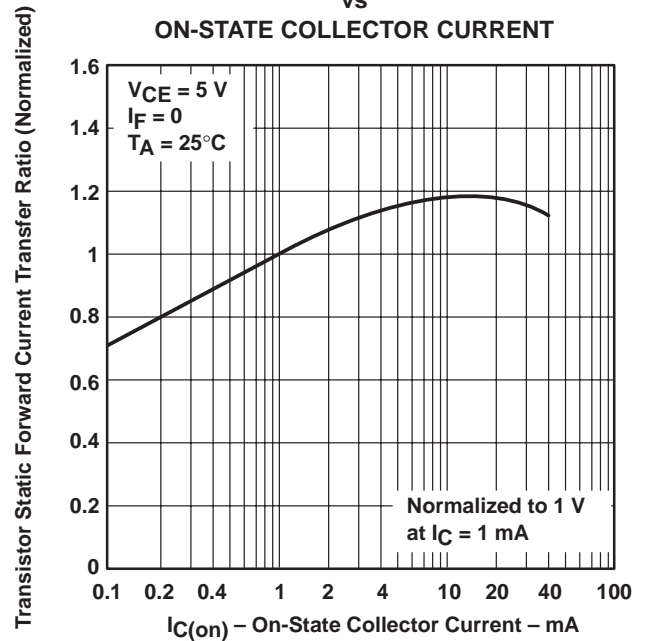
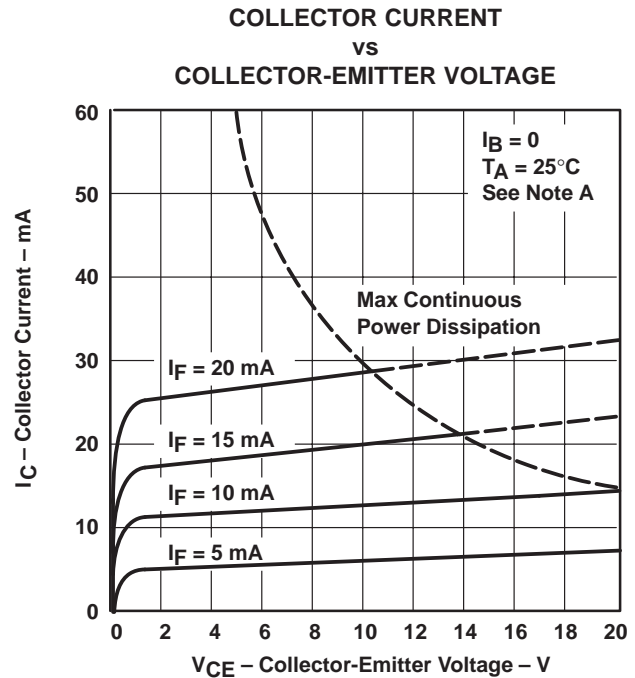
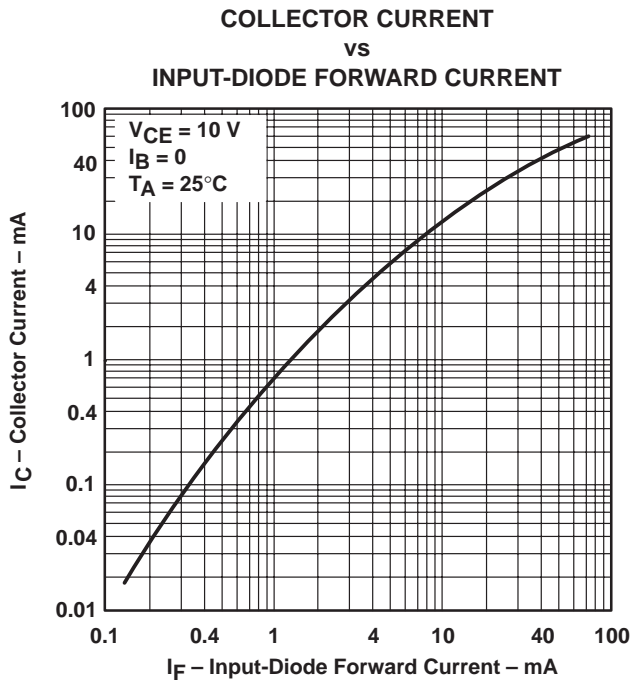
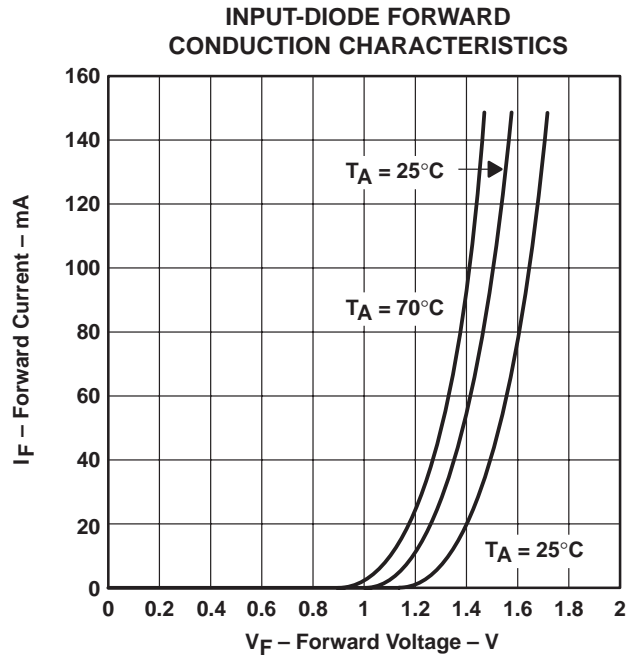
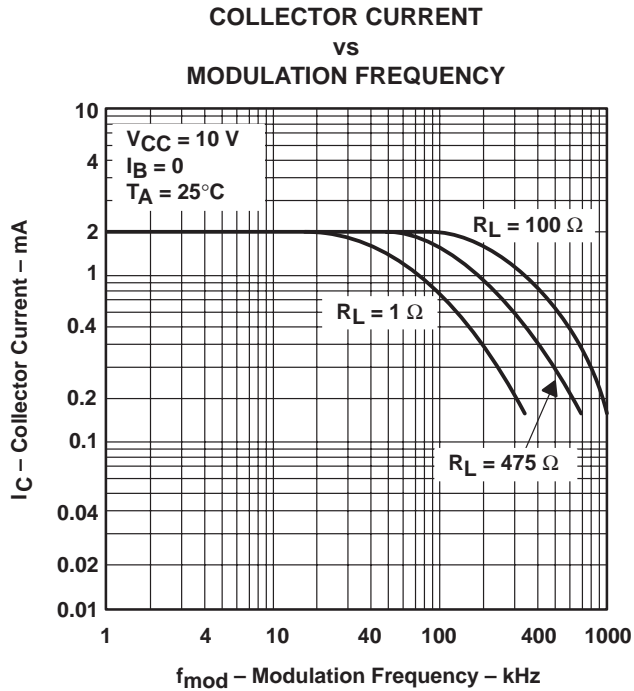


Figure 3

## TYPICAL CHARACTERISTICS



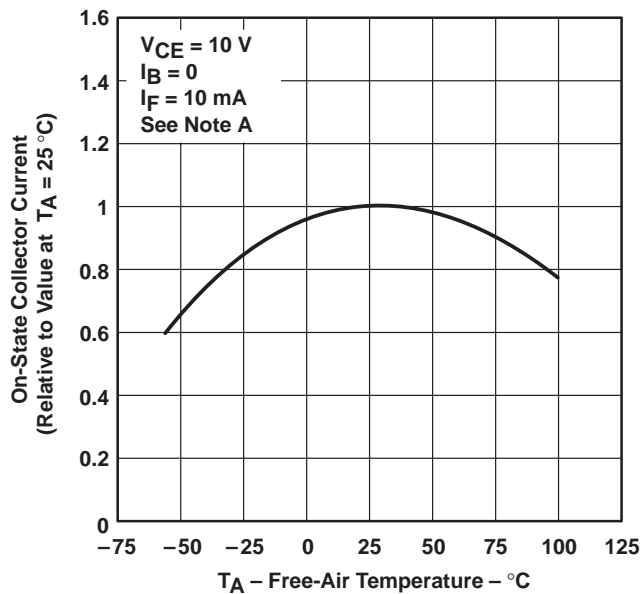
NOTE A. Pulse operation of input diode is required for operation beyond limits shown by dotted lines.

TYPICAL CHARACTERISTICS

ON-STATE COLLECTOR CURRENT  
(RELATIVE TO VALUE AT 25°C)

vs

FREE-AIR TEMPERATURE



NOTE A. These parameters were measured using pulse techniques,  $t_w = 1\text{ ms}$ , duty cycle  $\leq 2\%$ .

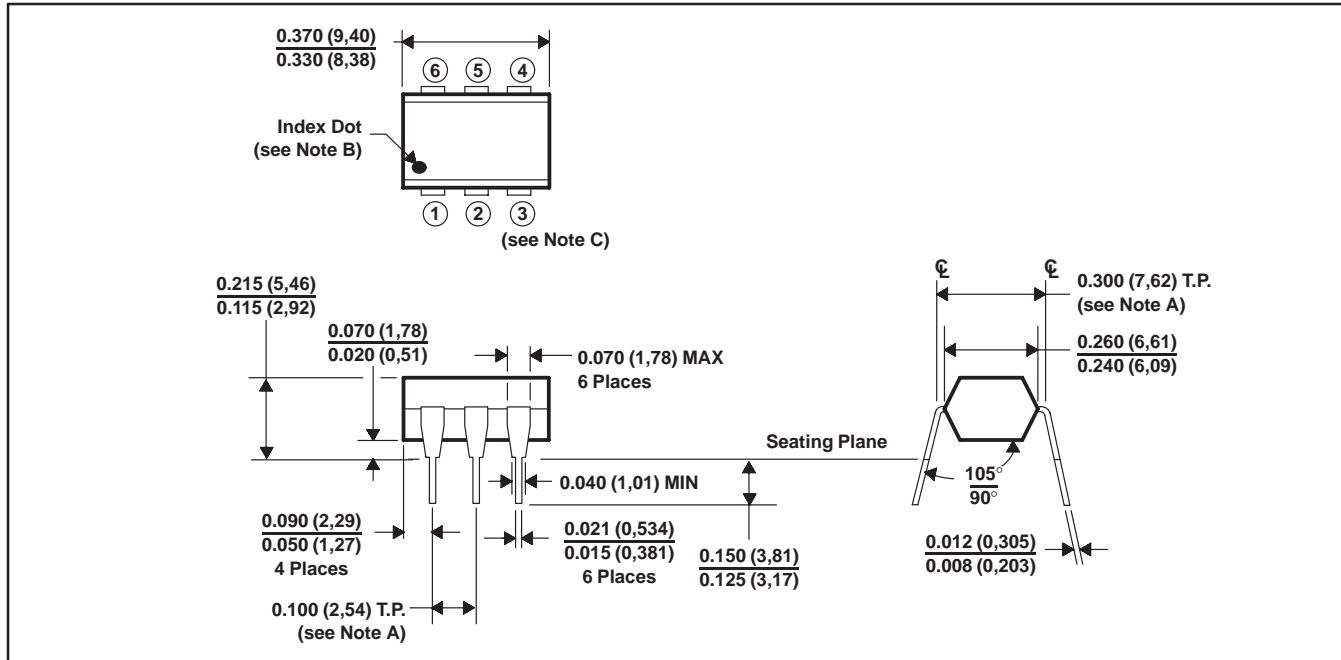
Figure 8

# 4N35, 4N36, 4N37 OPTOCOUPERS

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## APPLICATION INFORMATION

The devices consist of a gallium-arsenide infrared-emitting diode and an npn silicon phototransistor. Each device is available in a 6-terminal plastic dual-in-line package, shown in Figure 9, or in a DCJ plastic dual surface-mount optocoupler package (see Mechanical Data).



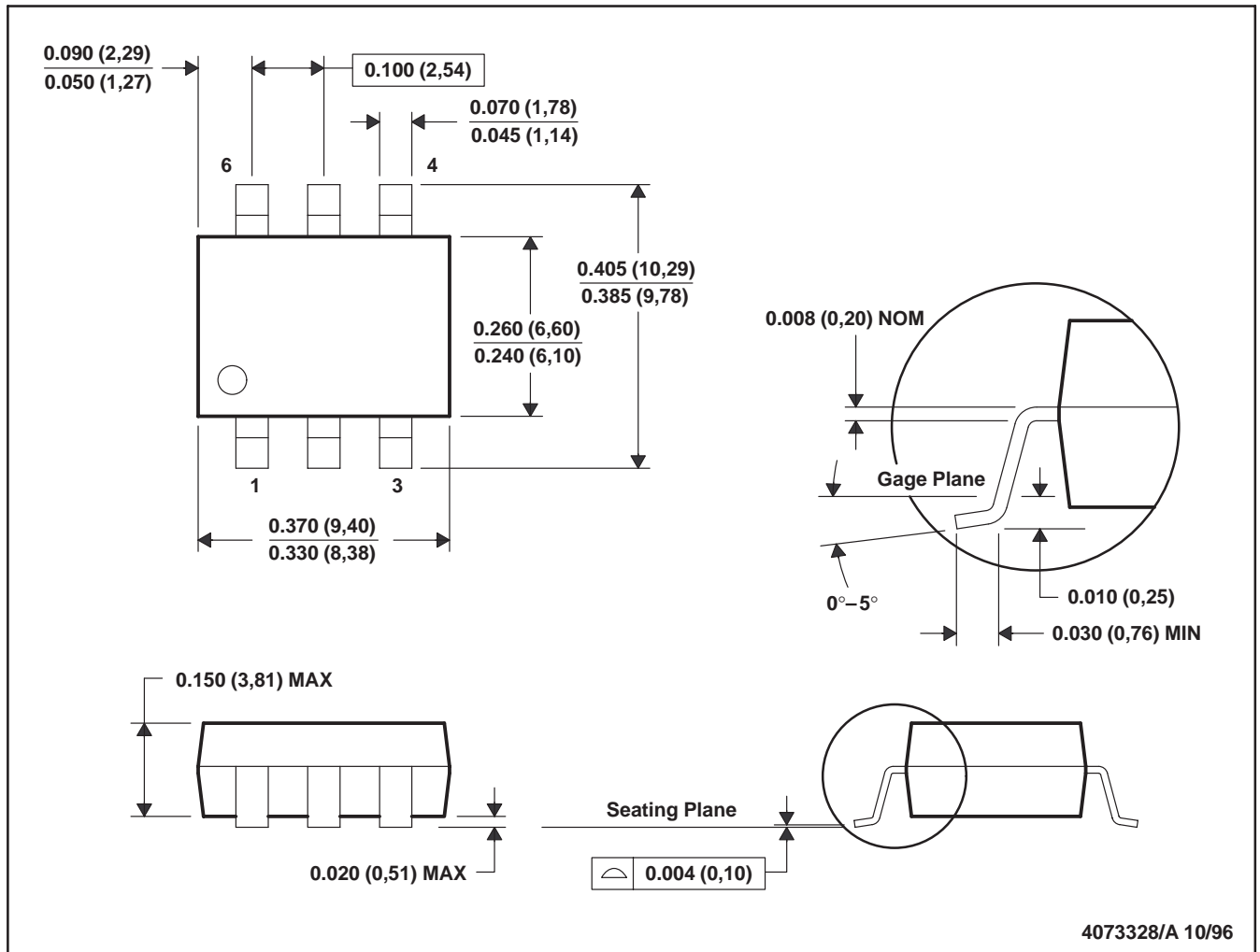
- NOTES: A. Terminals are within 0.005 (0,13) radius of true position (T.P.) with maximum material condition and unit installed.  
 B. Terminal 1 identified by index dot.  
 C. The dimensions given fall within JEDEC MO-001 AM dimensions.  
 D. All linear dimensions are in inches (millimeters).

Figure 9. Plastic Dual-in-Line Package

MECHANICAL DATA

DCJ (R-PDSO-G6)

PLASTIC DUAL SMALL-OUTLINE OPTOCOUPLER



- NOTES: A. All linear dimensions are in inches (millimeters)  
 B. This drawing is subject to change without notice.  
 C. Terminal 1 identified by index dot.

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